

# RJK0397DPA

30V, 30A, 10.1mΩ max.  
N Channel Power MOS FET  
High Speed Power Switching

R07DS0929EJ0400

Rev.4.00

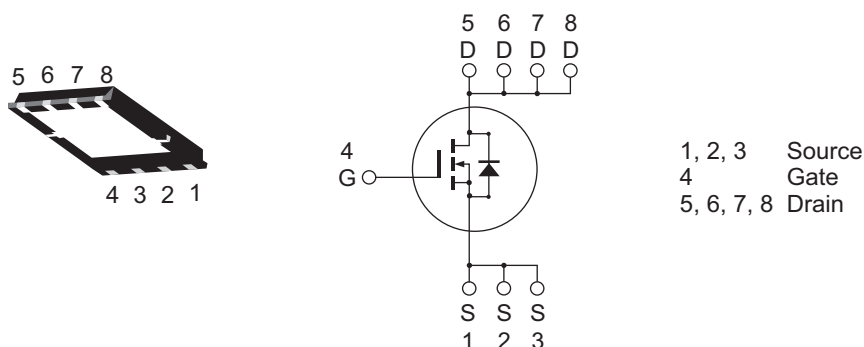
Mar 22, 2013

## Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
- Pb-free
- Halogen-free

## Outline

RENESAS Package code: PWSN0008DE-A  
(Package name: WPAK(3F))



## Absolute Maximum Ratings

(Ta = 25°C)

| Item                                   | Symbol                           | Ratings     | Unit |
|----------------------------------------|----------------------------------|-------------|------|
| Drain to source voltage                | $V_{DS}$                         | 30          | V    |
| Gate to source voltage                 | $V_{GS}$                         | ±20         | V    |
| Drain current                          | $I_D$                            | 30          | A    |
| Drain peak current                     | $I_{D(pulse)}$ <sup>Note1</sup>  | 120         | A    |
| Body-drain diode reverse drain current | $I_{DR}$                         | 30          | A    |
| Avalanche current                      | $I_{AP}$ <sup>Note 2</sup>       | 8           | A    |
| Avalanche energy                       | $E_{AR}$ <sup>Note 2</sup>       | 6.4         | mJ   |
| Channel dissipation                    | $P_{ch}$ <sup>Note3</sup>        | 25          | W    |
| Channel to case thermal impedance      | $\theta_{ch-c}$ <sup>Note3</sup> | 5           | °C/W |
| Channel temperature                    | $T_{ch}$                         | 150         | °C   |
| Storage temperature                    | $T_{stg}$                        | -55 to +150 | °C   |

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$   
2. Value at  $T_{ch} = 25^\circ C$ ,  $R_g \geq 50 \Omega$   
3.  $T_c = 25^\circ C$

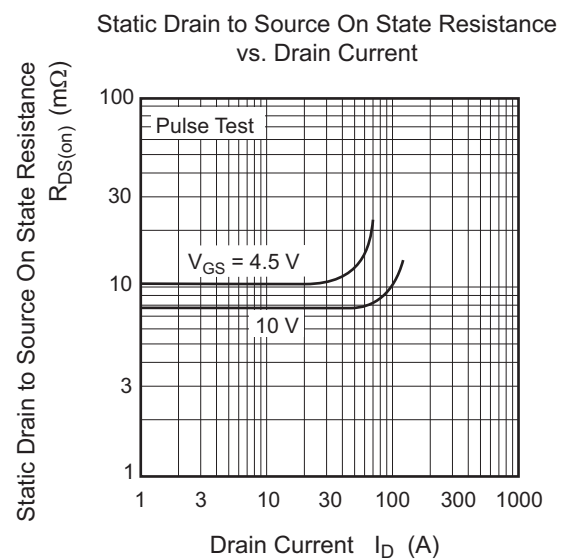
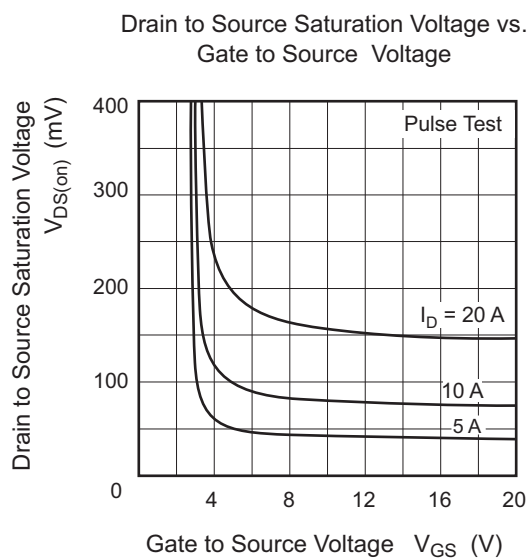
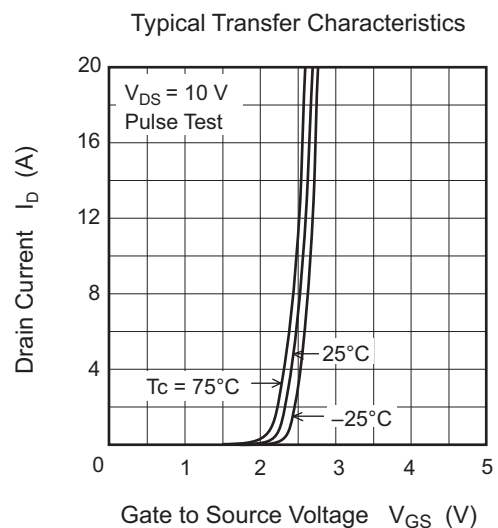
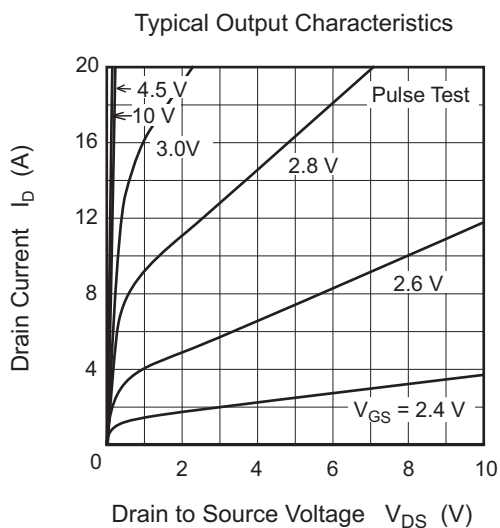
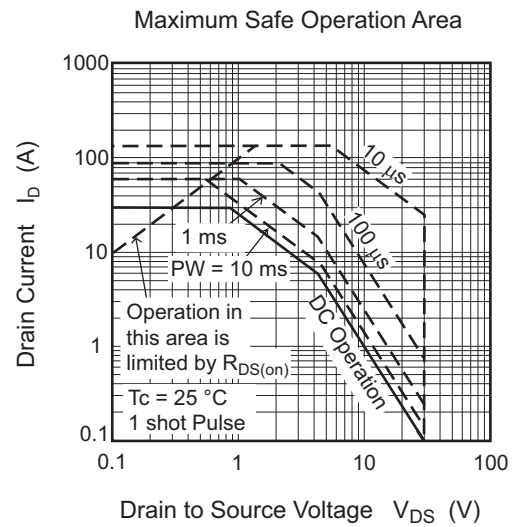
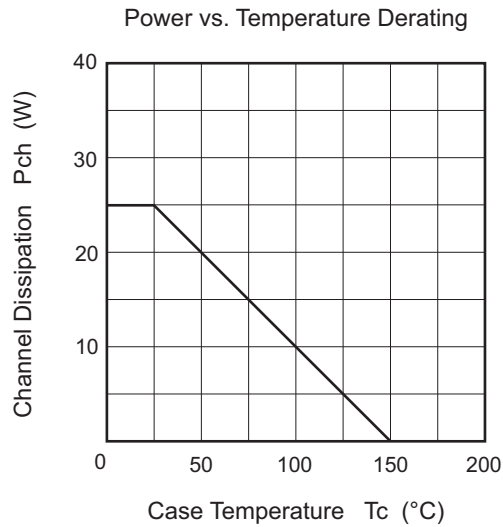
## Electrical Characteristics

(Ta = 25°C)

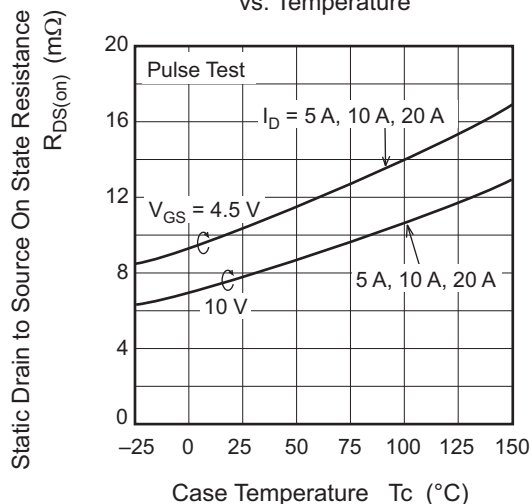
| Item                                       | Symbol        | Min | Typ  | Max       | Unit             | Test Conditions                                                              |
|--------------------------------------------|---------------|-----|------|-----------|------------------|------------------------------------------------------------------------------|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$ | 30  | —    | —         | V                | $I_D = 10 \text{ mA}$ , $V_{GS} = 0$                                         |
| Gate to source leak current                | $I_{GSS}$     | —   | —    | $\pm 0.1$ | $\mu\text{A}$    | $V_{GS} = \pm 20 \text{ V}$ , $V_{DS} = 0$                                   |
| Zero gate voltage drain current            | $I_{DSS}$     | —   | —    | 1         | $\mu\text{A}$    | $V_{DS} = 30 \text{ V}$ , $V_{GS} = 0$                                       |
| Gate to source cutoff voltage              | $V_{GS(off)}$ | 1.2 | —    | 2.5       | V                | $V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$                               |
| Static drain to source on state resistance | $R_{DS(on)}$  | —   | 7.8  | 10.1      | $\text{m}\Omega$ | $I_D = 15 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>              |
|                                            | $R_{DS(on)}$  | —   | 10.4 | 14.6      | $\text{m}\Omega$ | $I_D = 15 \text{ A}$ , $V_{GS} = 4.5 \text{ V}$ <sup>Note4</sup>             |
| Forward transfer admittance                | $ y_{fs} $    | —   | 65   | —         | S                | $I_D = 15 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note4</sup>              |
| Input capacitance                          | $C_{iss}$     | —   | 1110 | —         | pF               | $V_{DS} = 10 \text{ V}$                                                      |
| Output capacitance                         | $C_{oss}$     | —   | 160  | —         | pF               | $V_{GS} = 0$                                                                 |
| Reverse transfer capacitance               | $C_{rss}$     | —   | 80   | —         | pF               | $f = 1 \text{ MHz}$                                                          |
| Gate Resistance                            | $R_g$         | —   | 2.5  | —         | $\Omega$         |                                                                              |
| Total gate charge                          | $Q_g$         | —   | 7.4  | —         | nC               | $V_{DD} = 10 \text{ V}$                                                      |
| Gate to source charge                      | $Q_{gs}$      | —   | 3.2  | —         | nC               | $V_{GS} = 4.5 \text{ V}$                                                     |
| Gate to drain charge                       | $Q_{gd}$      | —   | 1.9  | —         | nC               | $I_D = 30 \text{ A}$                                                         |
| Turn-on delay time                         | $t_{d(on)}$   | —   | 8.8  | —         | ns               | $V_{GS} = 10 \text{ V}$ , $I_D = 15 \text{ A}$                               |
| Rise time                                  | $t_r$         | —   | 4    | —         | ns               | $V_{DD} \cong 10 \text{ V}$                                                  |
| Turn-off delay time                        | $t_{d(off)}$  | —   | 36   | —         | ns               | $R_L = 0.67 \Omega$                                                          |
| Fall time                                  | $t_f$         | —   | 5.1  | —         | ns               | $R_g = 4.7 \Omega$                                                           |
| Body-drain diode forward voltage           | $V_{DF}$      | —   | 0.88 | 1.15      | V                | $I_F = 30 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>                         |
| Body-drain diode reverse recovery time     | $t_{rr}$      | —   | 13   | —         | ns               | $I_F = 30 \text{ A}$ , $V_{GS} = 0$<br>$di_F/dt = 100 \text{ A}/\mu\text{s}$ |

Notes: 4. Pulse test

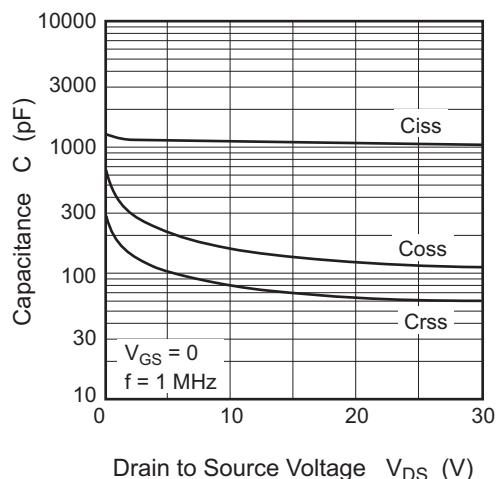
## Main Characteristics



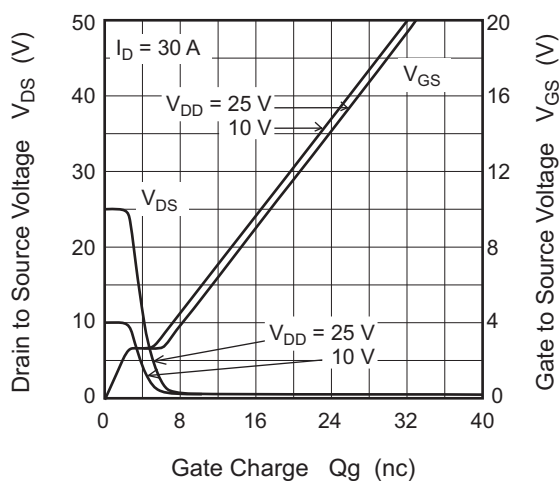
Static Drain to Source On State Resistance vs. Temperature



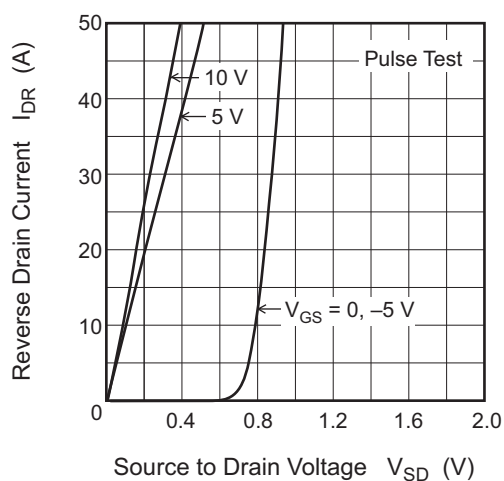
Typical Capacitance vs. Drain to Source Voltage



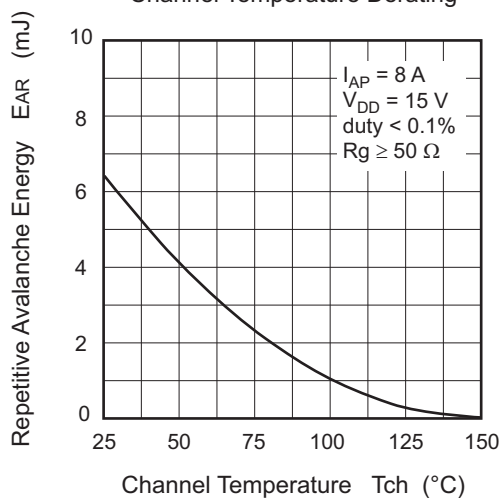
Dynamic Input Characteristics



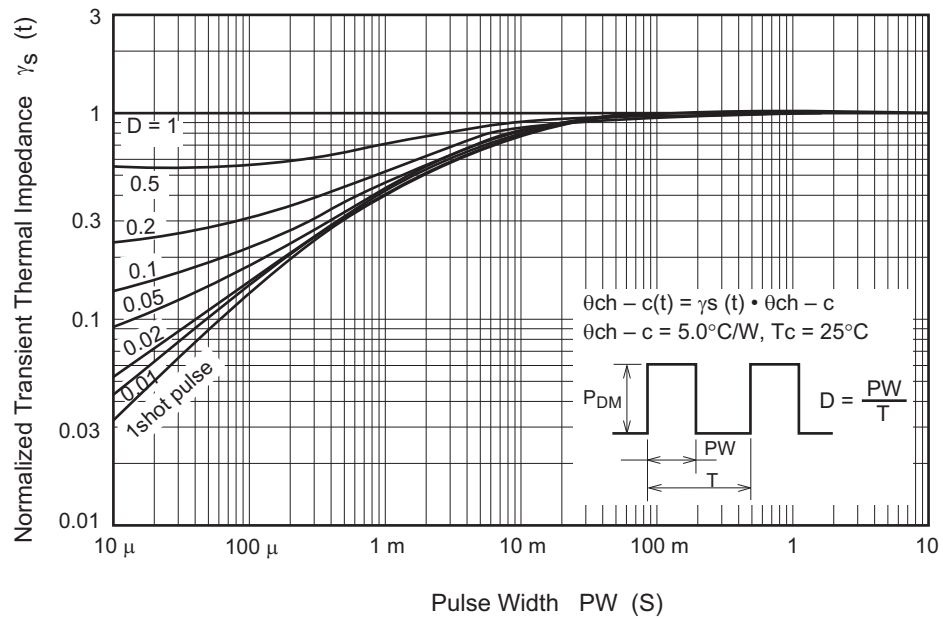
Reverse Drain Current vs. Source to Drain Voltage



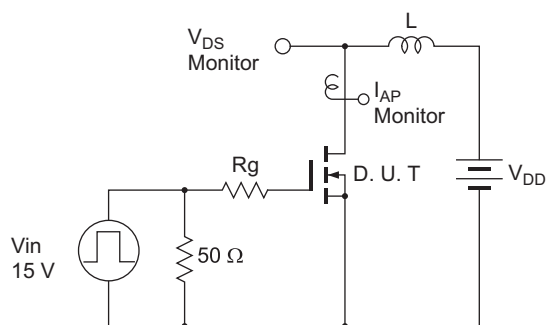
Maximum Avalanche Energy vs. Channel Temperature Derating



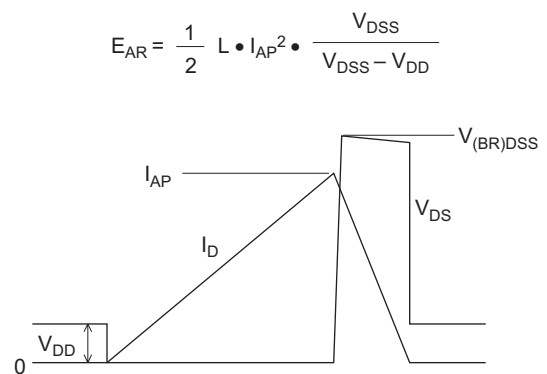
Normalized Transient Thermal Impedance vs. Pulse Width



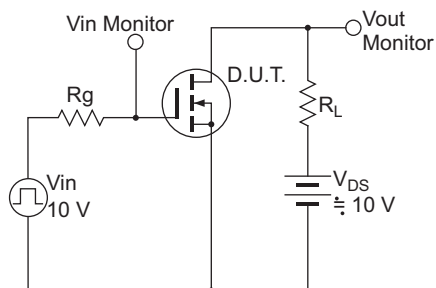
Avalanche Test Circuit



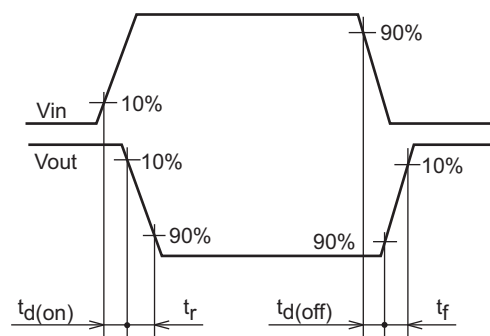
Avalanche Waveform



Switching Time Test Circuit



Switching Time Waveform



## Package Dimensions



## Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJK0397DPA-00-J5A     | 3000 pcs | Taping             |

Note: The symbol of 2nd "-" is occasionally presented as "#".

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